



PSMN8R5-100PS

N-channel 100 V 8.5 mΩ standard level MOSFET in TO220

17 October 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in a TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

3. Applications

- AC-to-DC power supply equipment
- Motor control
- Server power supplies
- Synchronous rectification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T _j = 25 °C; V _{GS} = 10 V; Fig. 1	[1]	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	-	263	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 13 ; Fig. 12		4.5	6.4	8.5	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; Fig. 14 ; Fig. 15		-	33	-	nC
Q _{G(tot)}	total gate charge			-	111	-	nC
Avalanche Ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 100 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; unclamped; Fig. 3		-	-	219	mJ

[1] Continuous current limited by package.

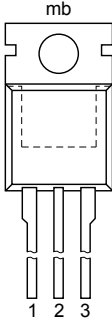
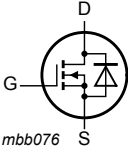


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-220AB (SOT78)	 mbb076
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN8R5-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN8R5-100PS	PSMN8R5-100PS

8. Limiting values

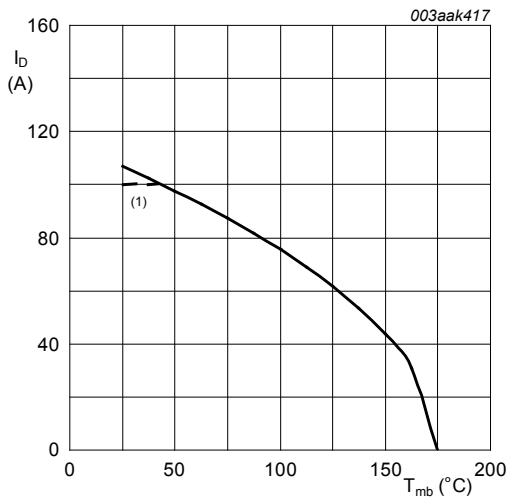
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$		-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_j = 25\text{ °C}$; Fig. 1	[1]	-	100	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 1		-	75	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 4		-	429	A

Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2		-	263	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	-	100	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$		-	429	A
Avalanche Ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 100\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; Fig. 3		-	219	mJ

[1] Continuous current limited by package.



(1) Capped at 100A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

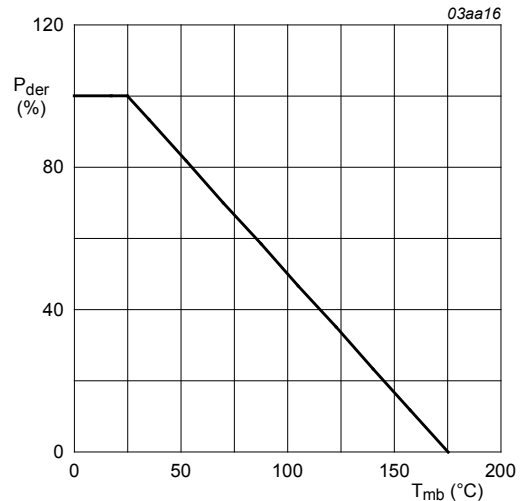


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

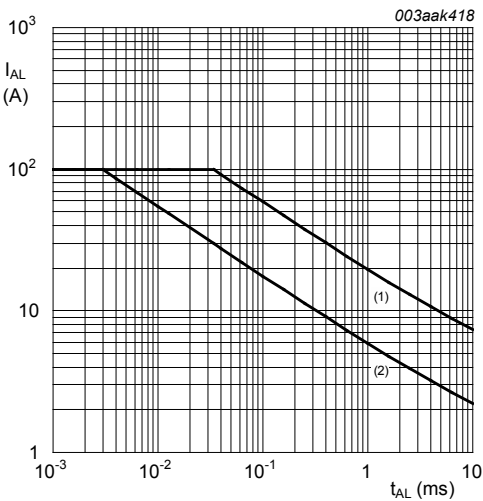


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j(jnt)} = 25^{\circ}C$; (2) $T_{j(jnt)} = 130^{\circ}C$

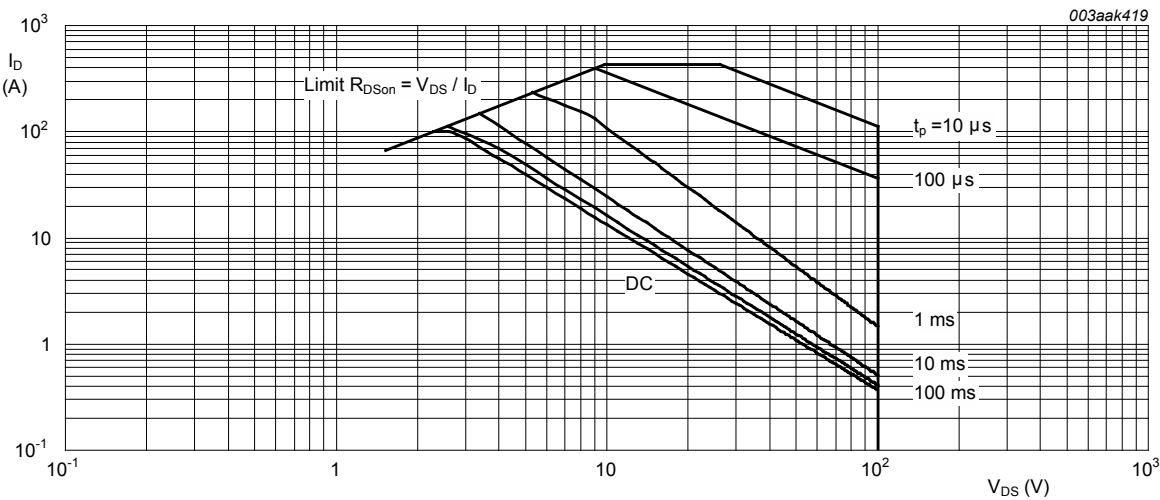


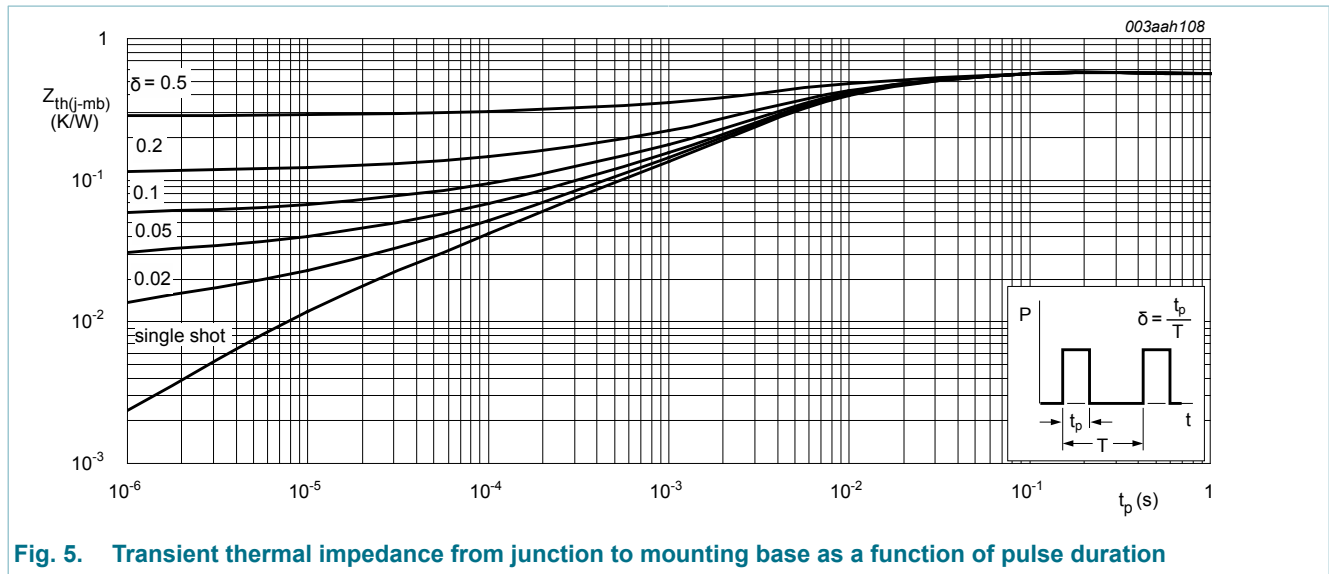
Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.49	0.57	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$	100	-	-	V
		$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_J = -55\ ^\circ\text{C}$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_J = 25\ ^\circ\text{C}$; Fig. 10 ; Fig. 11	2.4	3	4	V
V_{GSth}	gate-source threshold voltage	$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_J = 175\ ^\circ\text{C}$; Fig. 10	1	-	-	V
		$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_J = -55\ ^\circ\text{C}$; Fig. 10	-	-	4.5	V
I_{DSS}	drain leakage current	$V_{DS} = 100\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$	-	0.02	1	μA
		$V_{DS} = 100\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_J = 100\ ^\circ\text{C}$	-	-	20	μA
I_{GSS}	gate leakage current	$V_{GS} = -20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$	-	2	100	nA
		$V_{GS} = 20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_J = 175\ ^\circ\text{C}$; Fig. 12	-	16.95	22.6	mΩ
		$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_J = 100\ ^\circ\text{C}$; Fig. 12	-	11.18	14.9	mΩ
		$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_J = 25\ ^\circ\text{C}$; Fig. 13 ; Fig. 12	4.5	6.4	8.5	mΩ
R_G	gate resistance	$f = 1\ \text{MHz}$	0.36	0.71	1.42	Ω

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14 ; Fig. 15		-	111	-	nC
Q _{GS}	gate-source charge			-	24	-	nC
Q _{GS(th)}	pre-threshold gate-source charge			-	16	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge			-	8	-	nC
Q _{GD}	gate-drain charge			-	33	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 15 A; V _{DS} = 50 V; Fig. 14 ; Fig. 15		-	4.4	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 16 ; Fig. 17		-	5512	-	pF
C _{oss}	output capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 17		-	380	-	pF
C _{rss}	reverse transfer capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 16 ; Fig. 17		-	256	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; R _L = 2 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω		-	20	-	ns
t _r	rise time			-	35	-	ns
t _{d(off)}	turn-off delay time			-	87	-	ns
t _f	fall time			-	43	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 18		-	0.82	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;		-	53	-	ns
Q _r	recovered charge	V _{DS} = 50 V		-	124	-	nC

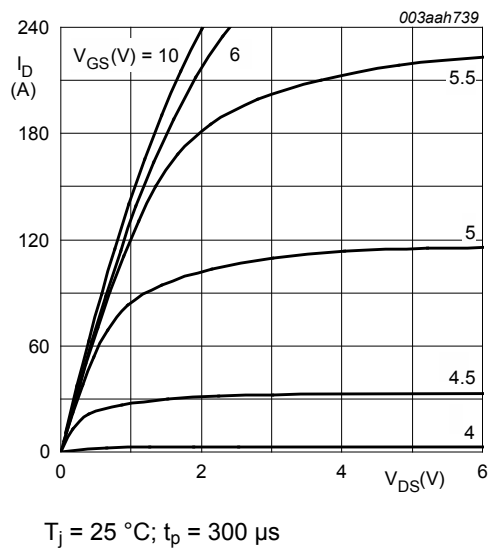


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

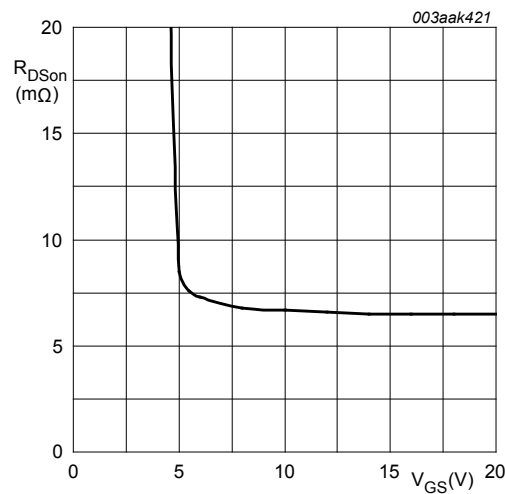


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

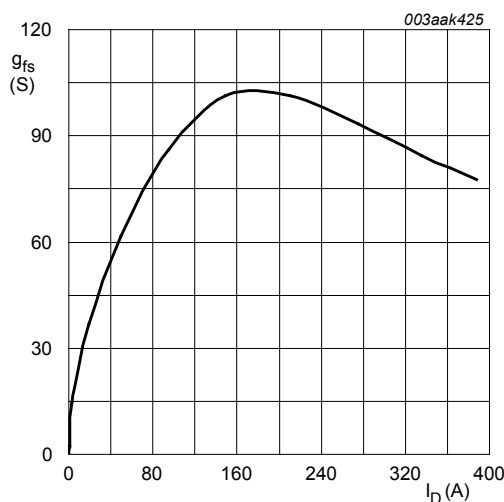


Fig. 8. Forward transconductance as a function of drain current; typical values

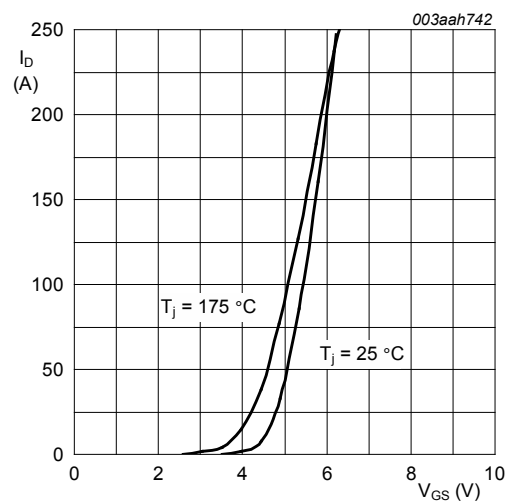


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

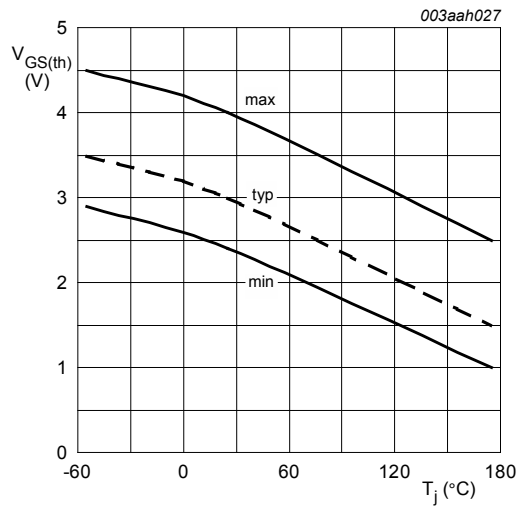


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

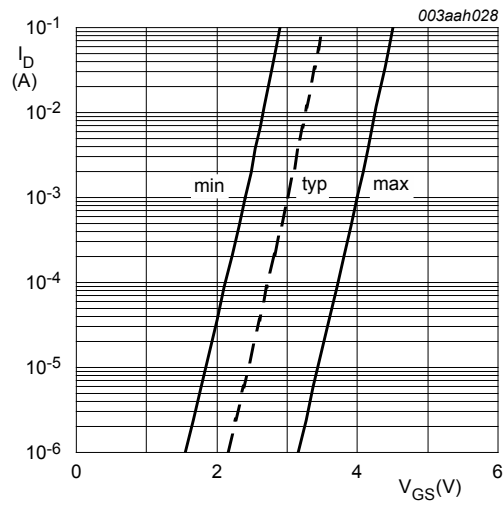


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{ V}$$

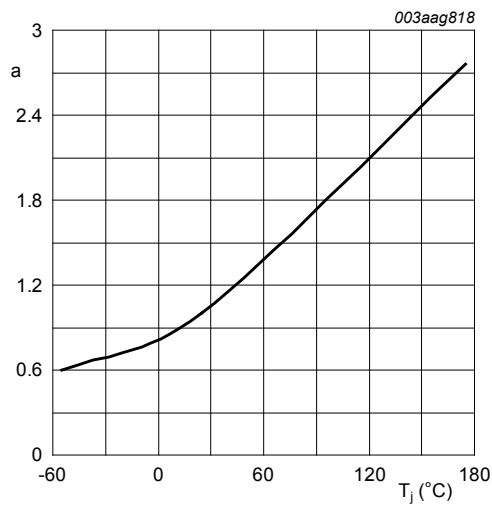


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

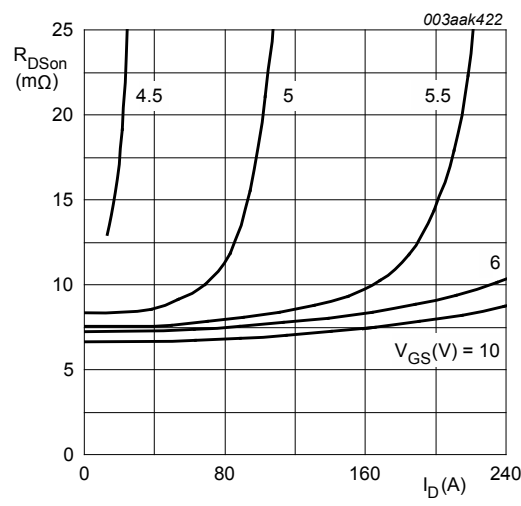


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}$$

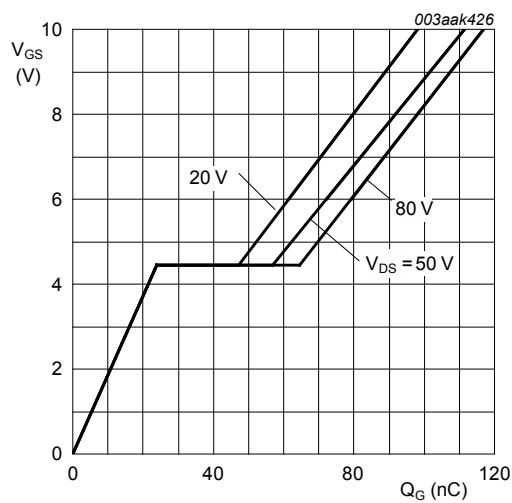


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

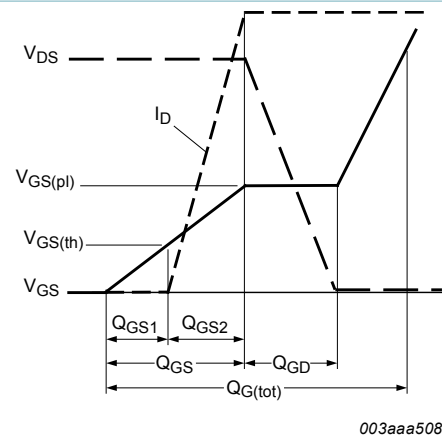


Fig. 15. Gate charge waveform definitions

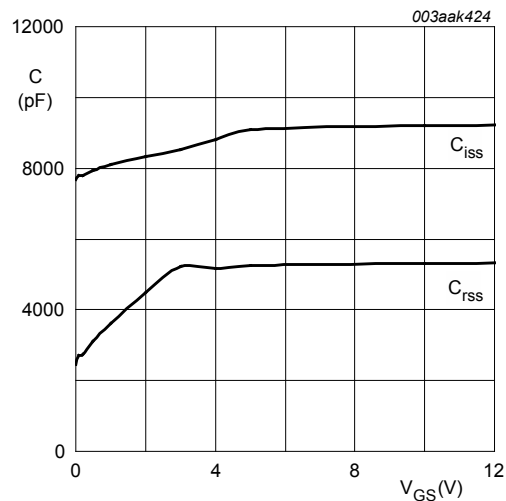


Fig. 16. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

$f = 1\text{ MHz}; V_{DS} = 0\text{ V}$

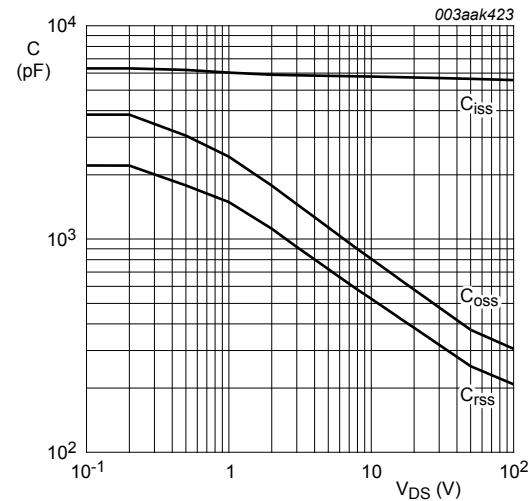


Fig. 17. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

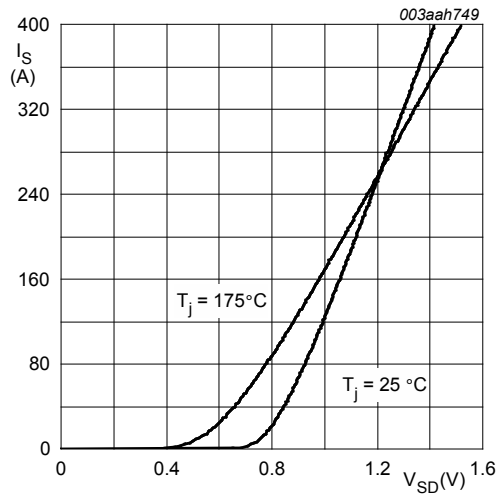


Fig. 18. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

11. Package outline

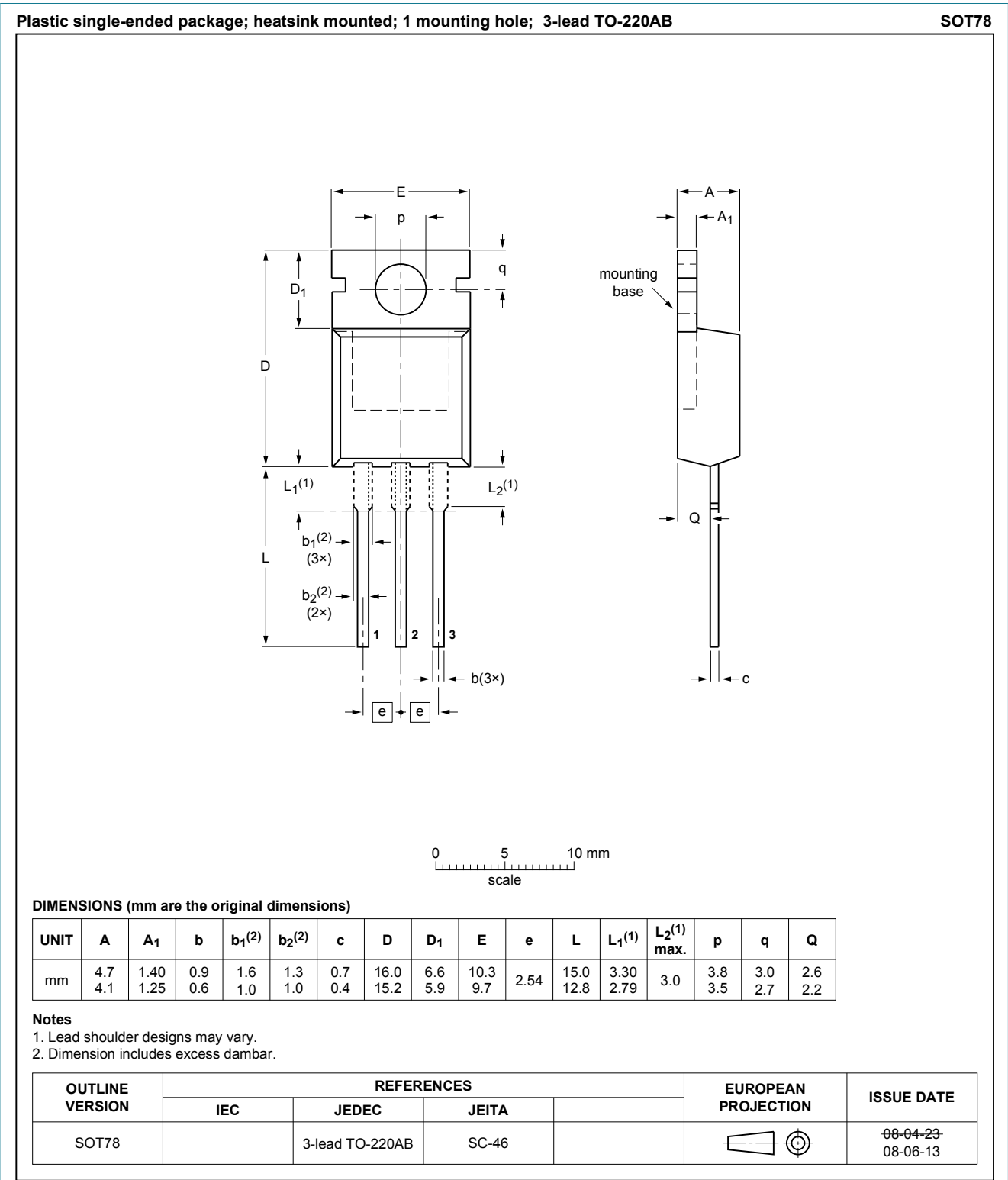


Fig. 19. Package outline TO-220AB (SOT78)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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